

### 32K x 8 LOW POWER CMOS STATIC RAM

**JULY 2015** 

#### **FEATURES**

- · Access time: 25 ns, 45 ns
- Low active power: 200 mW (typical)
- Low standby power
  - 150 μW (typical) CMOS standby
  - 15 mW (typical) operating
- Fully static operation: no clock or refresh required
- · TTL compatible inputs and outputs
- Single 5V power supply
- · Lead-free available
- Industrial and Automotive temperatures available

#### DESCRIPTION

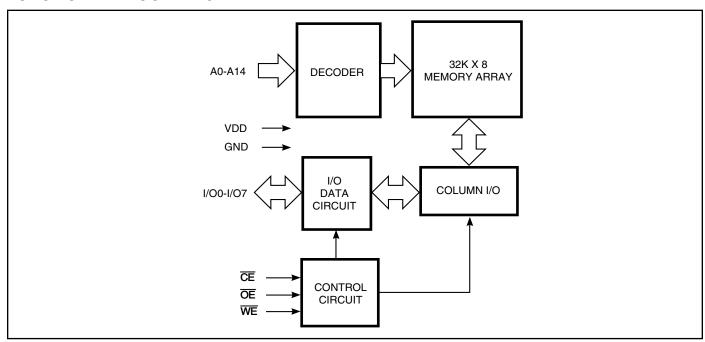
The *ISSI* IS62C256AL/IS65C256AL is a low power, 32,768 word by 8-bit CMOS static RAM. It is fabricated using *ISSI*'s high-performance, low power CMOS technology.

When  $\overline{\text{CE}}$  is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down to 150  $\mu$ W (typical) at CMOS input levels.

Easy memory expansion is provided by using an active LOW Chip Select ( $\overline{\text{CE}}$ ) input and an active LOW Output Enable ( $\overline{\text{OE}}$ ) input. The active LOW Write Enable ( $\overline{\text{WE}}$ ) controls both writing and reading of the memory.

The IS62C256AL/IS65C256AL is pin compatible with other 32Kx8 SRAMs in plastic SOP or TSOP (Type I) package.

#### **FUNCTIONAL BLOCK DIAGRAM**



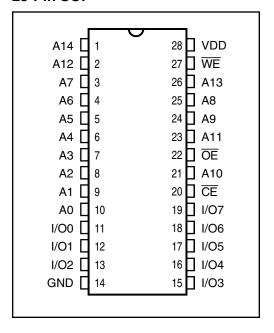
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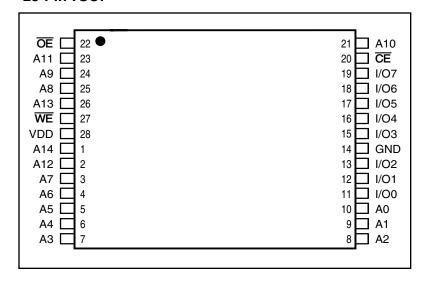
- a.) the risk of injury or damage has been minimized;
- o.) the user assume all such risks; and
- c.) potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances



## PIN CONFIGURATION 28-Pin SOP



## PIN CONFIGURATION 28-Pin TSOP



#### **PIN DESCRIPTIONS**

A0-A14	Address Inputs			
CE	Chip Select Input			
ŌĒ	Output Enable Input			
WE	Write Enable Input			
I/O0-I/O	I/O0-I/O7 Input/Output			
VDD	Power			
GND	Ground			

#### **TRUTH TABLE**

Mode	$\overline{\text{WE}}$	CE	ŌĒ	I/O Operation	VDD Current
Not Selected (Power-down)	Х	Н	Х	High-Z	ISB1, ISB2
Output Disabled	Н	L	Н	High-Z	lcc1, lcc2
Read	Н	L	L	<b>D</b> оит	lcc1, lcc2
Write	L	L	Χ	Din	Icc1, Icc2

#### ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Тѕтс	Storage Temperature	-65 to +150	°C
Рт	Power Dissipation	0.5	W
Іоит	DC Output Current (LOW)	20	mA

#### Note:

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



#### **OPERATING RANGE**

Part No.	Range	Ambient Temperature	<b>V</b> DD
IS62C256AL	Commercial	0°C to +70°C	5V ± 10%
IS62C256AL	Industrial	–40°C to +85°C	5V ± 10%
IS65C256AL	Automotive	–40°C to +125°C	5V ± 10%

#### DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	<b>Test Conditions</b>		Min.	Max.	Unit
Vон	Output HIGH Voltage	$V_{DD} = Min., I_{OH} = -1.0 \text{ mA}$		2.4	_	V
Vol	Output LOW Voltage	V <sub>DD</sub> = Min., I <sub>OL</sub> = 2.1 mA			0.4	V
ViH	Input HIGH Voltage			2.2	VDD + 0.5	V
VIL	Input LOW Voltage(1)			-0.3	0.8	V
ILI	Input Leakage	$GND \leq V IN \leq V DD$	Com.	-1	1	μA
			Ind.	-2	2	
			Auto.	-10	10	
ILO	Output Leakage	$GND \leq VOUT \leq VDD,$	Com.	-1	1	μA
		Outputs Disabled	Ind.	-2	2	
			Auto.	-10	10	

**Note:** 1.  $V_{IL} = -3.0V$  for pulse width less than 10 ns.



#### POWER SUPPLY CHARACTERISTICS<sup>(1)</sup> (Over Operating Range)

				-25	ns	-45	ns	
Symbol	Parameter	<b>Test Conditions</b>		Min.	Max.	Min.	Max.	Unit
lcc1	VDD Operating	$V_{DD} = Max., \overline{CE} = V_{IL}$	Com.	_	15	_	15	mA
	Supply Current	IOUT = 0  mA, f = 0	Ind.	_	20	_	20	
			Auto.	_	25		25	
lcc2	VDD Dynamic Operating	$V_{DD} = Max., \overline{CE} = V_{IL}$	Com.	_	25	_	20	mA
	Supply Current	IOUT = 0  mA, f = fMAX	Ind.	_	30	_	25	
			Auto.	_	35	_	30	
			typ. (2)		15	1	2	
IsB1	TTL Standby Current	VDD = Max.,	Com.	_	100	_	100	μA
	(TTL Inputs)	VIN = VIH  or  VIL	Ind.	_	120	_	120	
		$\overline{CE} \ge V_{IH}, f = 0$	Auto.	_	150	_	150	
IsB2	CMOS Standby	VDD = Max.,	Com.	_	15	_	15	μΑ
	Current (CMOS Inputs)	$\overline{CE} \ge V_{DD} - 0.2V$ ,	Ind.	_	20	_	20	
		$V_{IN} \ge V_{DD} - 0.2V$ , or	Auto.	_	50	_	50	
		$Vin \leq 0.2V, \ f = 0$	typ. (2)		5		5	

#### Note:

- 1. At f = fmax, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
- 2. Typical values are measured at VDD = 5.0V,  $TA = 25^{\circ}C$  and not 100% tested.

#### CAPACITANCE(1,2)

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	8	pF
Соит	Output Capacitance	Vout = 0V	10	pF

#### Notes:

- 1. Tested initially and after any design or process changes that may affect these parameters.
- 2. Test conditions:  $T_A = 25^{\circ}C$ , f = 1 MHz,  $V_{DD} = 5.0V$ .



#### READ CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup> (Over Operating Range)

		-25	ns	-45	ns		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
trc	Read Cycle Time	25	_	45	_	ns	
taa	Address Access Time	_	25	_	45	ns	
toha	Output Hold Time	2	_	2	_	ns	
tacs	CE Access Time	_	25	_	45	ns	
<b>t</b> DOE	OE Access Time		13	_	25	ns	
tLZOE <sup>(2)</sup>	OE to Low-Z Output	0	_	0	_	ns	
thzoe(2)	OE to High-Z Output	0	12	0	20	ns	
tLZCS <sup>(2)</sup>	CE to Low-Z Output	3	_	3	_	ns	
thzcs <sup>(2)</sup>	CE to High-Z Output	0	12	0	20	ns	
<b>t</b> PU <sup>(3)</sup>	CE to Power-Up	0	_	0	_	ns	
<b>t</b> PD <sup>(3)</sup>	CE to Power-Down	_	20	_	30	ns	

#### Notes:

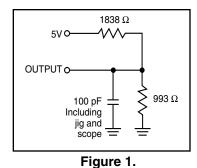
- 1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.

  2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
- 3. Not 100% tested.

#### **ACTEST CONDITIONS**

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Levels	1.5V
Output Load	See Figures 1 and 2

#### **ACTEST LOADS**



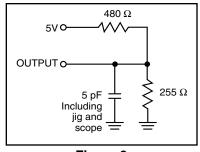
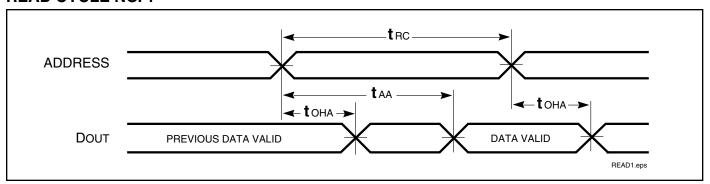


Figure 2.

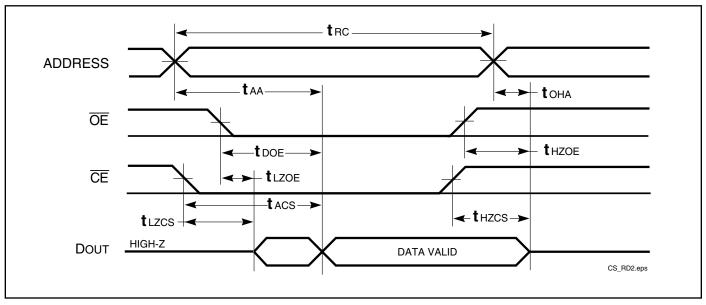


#### **AC WAVEFORMS**

#### **READ CYCLE NO. 1<sup>(1,2)</sup>**



#### **READ CYCLE NO. 2**<sup>(1,3)</sup>



- Notes:
  1. WE is HIGH for a Read Cycle.
- 2. The device is continuously selected.  $\overline{OE}$ ,  $\overline{CE} = V_{IL}$ .
- 3. Address is valid prior to or coincident with  $\overline{\text{CE}}$  LOW transitions.



#### WRITE CYCLE SWITCHING CHARACTERISTICS(1,3) (Over Operating Range)

		-25	ns	-45	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
twc	Write Cycle Time	25	_	45	_	ns
tscs	CE to Write End	15	_	35	_	ns
taw	Address Setup Time to Write End	15	_	25	_	ns
<b>t</b> HA	Address Hold from Write End	0	_	0	_	ns
<b>t</b> sa	Address Setup Time	0	_	0	_	ns
tPWE <sup>(4)</sup>	WE Pulse Width	15	_	25	_	ns
tsp	Data Setup to Write End	12	_	20	_	ns
<b>t</b> HD	Data Hold from Write End	0	_	0	_	ns
thzwe <sup>(2)</sup>	WE LOW to High-Z Output	_	8	_	20	ns
tLzwe <sup>(2)</sup>	WE HIGH to Low-Z Output	0		0	_	ns

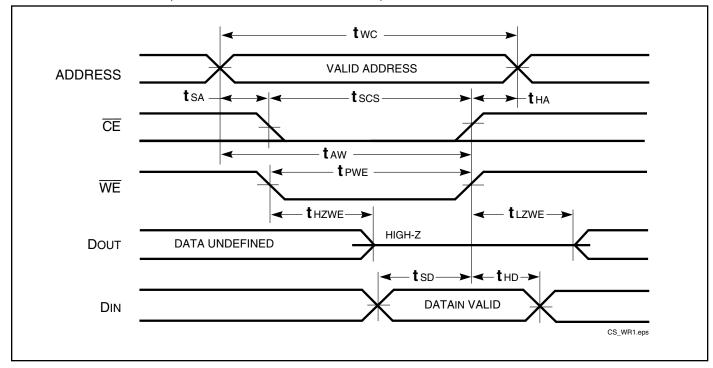
#### Notes:

- 1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
- 2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
- 3. The internal write time is defined by the overlap of CE LOW and WE LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.

  4. Tested with OE HIGH.

#### **AC WAVEFORMS**

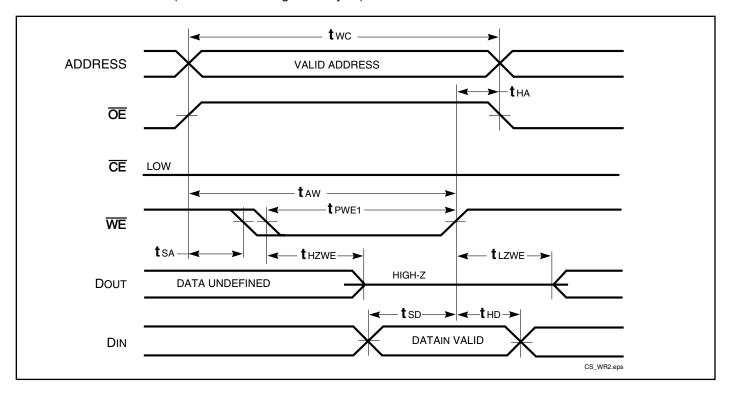
#### WRITE CYCLE NO. 1 (CE Controlled, OE is HIGH or LOW) (1)



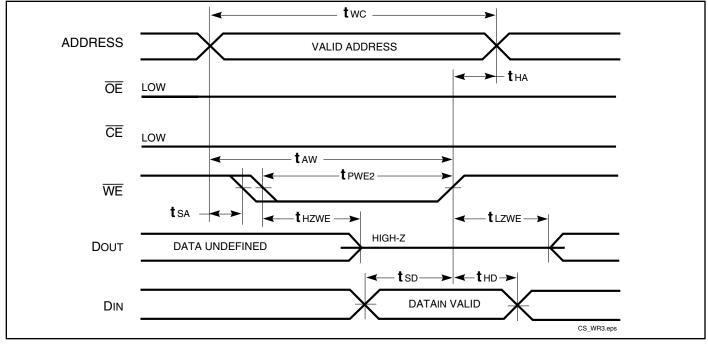
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#### **AC WAVEFORMS**

#### WRITE CYCLE NO. 2 (OE is HIGH During Write Cycle) (1,2)



#### WRITE CYCLE NO. 3 (OE is LOW During Write Cycle) (1)



#### Notes:

- 1. The internal write time is defined by the overlap of  $\overline{\text{CE}}$  LOW and  $\overline{\text{WE}}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
- 2. I/O will assume the High-Z state if  $\overline{OE} = V_{IH}$ .

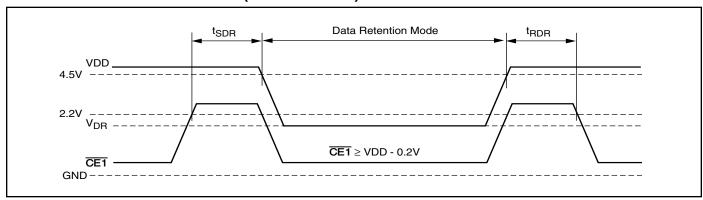


#### **DATA RETENTION SWITCHING CHARACTERISTICS**

Symbol	Parameter	Test Condition		Min.	Тур.	Max.	Unit
V <sub>DR</sub>	VDD for Data Retention	See Data Retention Waveform		2.0		5.5	V
IDR	Data Retention Current	$V_{DD} = 2.0V$ , $\overline{CE} \ge V_{DD} - 0.2V$ $V_{IN} \ge V_{DD} - 0.2V$ , or $V_{IN} \le V_{SS} + 0.2V$	Com. Ind.	_	_	15 20	μA
			Auto.	_	_	50	
tsdr	Data Retention Setup Time	See Data Retention Waveform		0		_	ns
trdr	Recovery Time	See Data Retention Waveform		trc		_	ns

#### Note:

### DATA RETENTION WAVEFORM (CE Controlled)



<sup>1.</sup> Typical Values are measured at  $V_{DD} = 5V$ ,  $T_A = 25^{\circ}C$  and not 100% tested.



#### **ORDERING INFORMATION**

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part No.	Package
45	IS62C256AL-45T	TSOP
	IS62C256AL-45TL	TSOP, Lead-free
	IS62C256AL-45UL	Plastic SOP, Lead-free

#### **ORDERING INFORMATION**

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
25	IS62C256AL-25TI IS62C256AL-25ULI	TSOP Plastic SOP, Lead-free
45	IS62C256AL-45TI IS62C256AL-45TLI IS62C256AL-45ULI	TSOP TSOP, Lead-free Plastic SOP, Lead-free

#### **ORDERING INFORMATION**

Automotive Range: -40°C to +125°C

Speed (ns)	Order Part No.	Package
25	IS65C256AL-25TA3 IS65C256AL-25TLA3 IS65C256AL-25ULA3	TSOP TSOP, Lead-free Plastic SOP, Lead-free
45	IS65C256AL-45TA3 IS65C256AL-45TLA3 IS65C256AL-45ULA3	TSOP TSOP, Lead-free Plastic SOP, Lead-free



